

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	18	on adj resistance and ("TFT" or "MOS" or "MOSFET" or "FET" or transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:06
L2	36	on adj resistance and ("TFT" or "MOS" or "MOSFET" or "FET" or transistor or switch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:06
L3	0	2 and epitaxial	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:05
L4	0	on adj resistance and epitaxial	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:06
L5	33036	resistance and epitaxial	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:06
L6	5512	resistance and epitaxial and breakdown adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:06
L7	5073	6 and ("TFT" or "MOS" or "MOSFET" or "FET" or transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:06
L8	5133	6 and ("TFT" or "MOS" or "MOSFET" or "FET" or transistor or switch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:07

L9	1909	8 and thickness with epitaxial	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:12
L10	1707	9 and (active or source)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:08
L11	1416	10 and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:08
L12	1314	10 and ((reduc\$4 or lower\$4 or drop\$4) with resistance)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:09
L13	395	10 and ((reduc\$4 or lower\$4 or drop\$4) with resistance) same ((increas\$4 or high\$4 or rais\$4) with breakdown adj voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:12
L14	1	13 and dopant adj density	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:12
L15	896	257/328.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:12
L16	159	15 and thickness with epitaxial	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:22

L17	45	16 and ((reduc\$4 or lower\$4 or drop\$4) with resistance) same ((increas\$4 or high\$4 or rais\$4) with breakdown adj voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:18
L18	0	16 and ((reduc\$4 or lower\$4 or drop\$4) with on adj resistance) same ((increas\$4 or high\$4 or rais\$4) with breakdown adj voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:16
L20	0	16 and ((reduc\$4 or lower\$4 or drop\$4) with "ON" adj resistance) same ((increas\$4 or high\$4 or rais\$4) with breakdown adj voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:17
L21	0	16 and ((reduc\$4 or lower\$4 or drop\$4) with "ON-" adj resistance) same ((increas\$4 or high\$4 or rais\$4) with breakdown adj voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:17
L22	12	16 and ((reduc\$4 or lower\$4 or drop\$4) with resistance) same ((increas\$4 or high\$4 or rais\$4) with breakdown adj voltage) same epitaxial with thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:19
L23	4	16 and ((reduc\$4 or lower\$4 or drop\$4) with resistance) same ((increas\$4 or high\$4 or rais\$4) with breakdown adj voltage) same epitaxial with thickness and terminat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:28
L24	2	15 and thickness with epitaxial with terminat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:26
L25	0	257/330. "ccls."	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:26

L26	1195	257/330.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:26
L27	410	257/332.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:26
L28	138	257/502.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:26
L29	5	26 and thickness with epitaxial with terminat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:27
L30	0	27 and thickness with epitaxial with terminat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:26
L31	1	28 and thickness with epitaxial with terminat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:27
L32	3	29 and ((reduc\$4 or lower\$4 or drop\$4) with resistance) same ((increas\$4 or high\$4 or rais\$4) with breakdown adj voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 14:28